

ZXM66P03N8

30V P-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS} = -30V$; $R_{DS(ON)} = 0.025\Omega$; $I_D = -7.9A$

DESCRIPTION

This new generation of high density MOSFETs from Zetex utilises a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Low profile SOIC package

APPLICATIONS

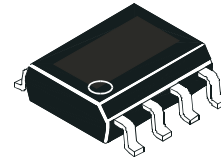
- DC - DC converters
- Power management functions
- Disconnect switches
- Motor control

ORDERING INFORMATION

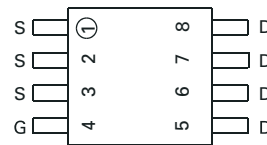
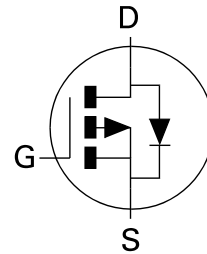
DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXM66P03N8TA	7"	12mm	500 units
ZXM66P03N8TC	13"	12mm	2500 units

DEVICE MARKING

- ZXM
66P03



SO8



Top View

ZXM66P03N8

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	-30	V
Gate- Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $V_{GS}=-10V$; $T_A=25^\circ C$ (b) $V_{GS}=-10V$; $T_A=70^\circ C$ (b) $V_{GS}=-10V$; $T_A=25^\circ C$ (a)	I_D	-7.9 -6.3 -6.25	A
Pulsed Drain Current (c)	I_{DM}	-28	A
Continuous Source Current (Body Diode)(b)	I_S	-4.1	A
Pulsed Source Current (Body Diode)(c)	I_{SM}	-28	A
Power Dissipation at $T_A=25^\circ C$ (a) Linear Derating Factor	P_D	1.56 12.5	W mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (b) Linear Derating Factor	P_D	2.5 20	W mW/ $^\circ C$
Operating and Storage Temperature Range	T_j : T_{stg}	-55 to +150	$^\circ C$

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	80	$^\circ C/W$
Junction to Ambient (b)	$R_{\theta JA}$	50	$^\circ C/W$

NOTES

- (a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions
(b) For a device surface mounted on FR4 PCB measured at $t \leq 10$ secs.
(c) Repetitive rating 25mm x 25mm FR4 PCB, $D = 0.05$, pulse width 10 μs - pulse width limited by maximum junction temperature.



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ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	-30			V	$I_D = -250\mu\text{A}, V_{GS} = 0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}			-1	μA	$V_{DS} = -24\text{V}, V_{GS} = 0\text{V}$
Gate-Body Leakage	I_{GSS}			-100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	-1.0			V	$I_D = -250\mu\text{A}, V_{DS} = V_{GS}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$			0.025 0.035	Ω Ω	$V_{GS} = -10\text{V}, I_D = -5.6\text{A}$ $V_{GS} = -4.5\text{V}, I_D = -2.8\text{A}$
Forward Transconductance (1)(3)	g_{fs}		14.4		S	$V_{DS} = -15\text{V}, I_D = -5.6\text{A}$
DYNAMIC (3)						
Input Capacitance	C_{iss}		1979		pF	$V_{DD} = -25\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Output Capacitance	C_{oss}		743		pF	
Reverse Transfer Capacitance	C_{rss}		279		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	$t_{d(on)}$		7.6		ns	$V_{DD} = -15\text{V}, I_D = -5.6\text{A}$ $R_G = 6.2\Omega, V_{GS} = -10\text{V}$
Rise Time	t_r		16.3		ns	
Turn-Off Delay Time	$t_{d(off)}$		94.6		ns	
Fall Time	t_f		39.6		ns	
Gate Charge	Q_g		36		nC	$V_{DS} = -15\text{V}, V_{GS} = -5\text{V}$ $I_D = -5.6\text{A}$
Total Gate Charge	Q_g		62.5		nC	$V_{DS} = -15\text{V}, V_{GS} = -10\text{V}$ $I_D = -5.6\text{A}$
Gate-Source Charge	Q_{gs}		4.9		nC	
Gate Drain Charge	Q_{gd}		19.6		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V_{SD}			-0.95	V	$T_j = 25^{\circ}\text{C}, I_S = -5.6\text{A}, V_{GS} = 0\text{V}$
Reverse Recovery Time (3)	t_{rr}		35		ns	$T_j = 25^{\circ}\text{C}, I_F = -5.6\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge(3)	Q_{rr}		39.9		nC	

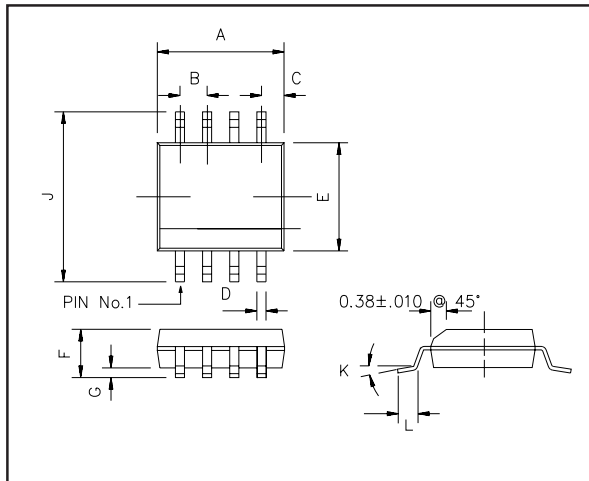
(1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$.

(2) Switching characteristics are independent of operating junction temperature.

(3) For design aid only, not subject to production testing.

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PACKAGE DIMENSIONS



DIM	Millimetres		Inches	
	Min	Max	Min	Max
A	4.80	4.98	0.189	0.196
B	1.27 BSC		0.05 BSC	
C	0.53 REF		0.02 REF	
D	0.36	0.46	0.014	0.018
E	3.81	3.99	0.15	0.157
F	1.35	1.75	0.05	0.07
G	0.10	0.25	0.004	0.010
J	5.80	6.20	0.23	0.24
K	0°	8°	0°	8°
L	0.41	1.27	0.016	0.050

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